Hamaida Kheira, Int J Mater Sci Res. 2018 http://dx.doi.org/10.18689/2638-1559.a2.002



2nd International Conference on ge Materials Science and Research

September 26-27, 2018 Frankfurt, Germany

Analyis by AES and EELS Spectroscopy of InPO₄ and In,O₃ Developed on InP Substrate

Hamaida Kheira

University Center BELHADJ Bouchaïb, Algeria

The indium oxide In_2O_3 and $InPO_4$ are the transparent conducting ovidés (T.C.O) appropriate to several applications in optoelectronic field.

The irradiation by 4keV Energy on the InP substrate led to genereate two oxides such as $InPO_4$ and In_2O_3 . Developed on the InP. Owing the both methods of Analyis, Auger Electron Spectroscopy (AES) and Electron Energy Loss Spectroscopy (EELS) thy can detected the presence of these oxides. When using the treatments by Casa XPS and webPlotDigezer softwares, the quantities of $InPO_4$ and In_2O_3 have been estimated according to the time of electron irradiation.